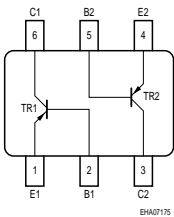
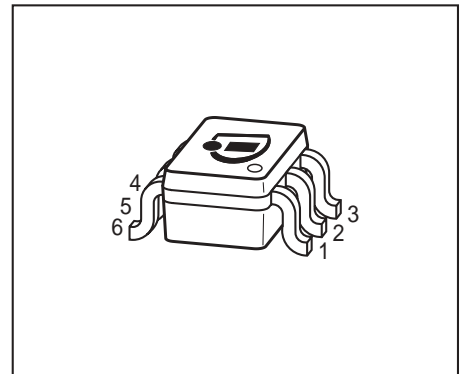


PNP Silicon AF Transistor Array

- Precision matched transistor pair: $\Delta I_C \leq 10\%$
- For current mirror applications
- Low collector-emitter saturation voltage
- Two (galvanic) internal isolated Transistors
- Complementary type: BCM846S
- BCM856S: For orientation in reel see package information below
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



Type	Marking	Pin Configuration					Package	
BCM856S	3Ms	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	65	V
Collector-emitter voltage	V_{CES}	80	
Collector-base voltage	V_{CBO}	80	
Emitter-base voltage	V_{EBO}	5	
Collector current	I_C	100	mA
Peak collector current	I_{CM}	200	
Total power dissipation- $T_S = 115\text{ °C}$	P_{tot}	250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

¹Pb-containing package may be available upon special request

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	140	K/W

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 10 \text{ mA}, I_B = 0 \text{ A}$	$V_{(BR)CEO}$	65	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0 \text{ A}$	$V_{(BR)CBO}$	80	-	-	
Collector-emitter breakdown voltage $I_C = 10 \mu\text{A}, V_{BE} = 0 \text{ A}$	$V_{(BR)CES}$	80	-	-	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}, I_C = 0 \text{ A}$	$V_{(BR)EBO}$	5	-	-	
Collector-base cutoff current $V_{CB} = 30 \text{ V}, I_E = 0 \text{ A}$ $V_{CB} = 30 \text{ V}, I_E = 0 \text{ A}, T_A = 150 \text{ }^\circ\text{C}$	I_{CBO}	-	-	0.015 5	μA
DC current gain ⁻²⁾ $I_C = 10 \mu\text{A}, V_{CE} = 5 \text{ V}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$	h_{FE}	- 200	250 290	- 450	-
Collector-emitter saturation voltage ²⁾ $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$ $I_C = 100 \text{ mA}, I_B = 5 \text{ mA}$	V_{CEsat}	- -	90 250	300 650	mV
Base emitter saturation voltage ²⁾ $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$ $I_C = 100 \text{ mA}, I_B = 5 \text{ mA}$	V_{BEsat}	- -	700 850	- -	
Base-emitter voltage ⁻²⁾ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	$V_{BE(ON)}$	600 -	650 -	750 820	
Matching $I_B = 1 \mu\text{A}, V_{CE1} = V_{CE2} = 1.0\text{V}$ $I_B = 100 \mu\text{A}, V_{CE1} = V_{CE2} = 1.0\text{V}$	ΔI_C	-10 -10	- -	10 10	%

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

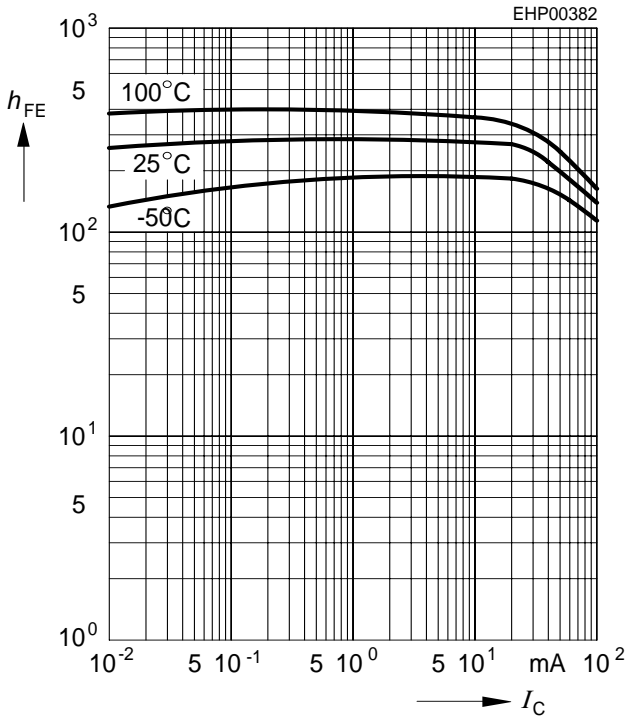
²Puls test: $t < 300\mu\text{s}; D < 2\%$

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $I_C = 20 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	f_T	-	250	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{cb}	-	3	-	pF
Emitter-base capacitance $V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}$	C_{eb}	-	8	-	
Short-circuit input impedance $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$	h_{11e}	-	4.5	-	k Ω
Open-circuit reverse voltage transf. ratio $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$	h_{12e}	-	2	-	10^{-4}
Short-circuit forward current transf. ratio $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$	h_{21e}	-	330	-	-
Open-circuit output admittance $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$	h_{22e}	-	30	-	μS
Noise figure $I_C = 200 \mu\text{A}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz},$ $\Delta f = 200 \text{ Hz}, R_S = 2 \text{ k}\Omega$	F	-	-	10	dB

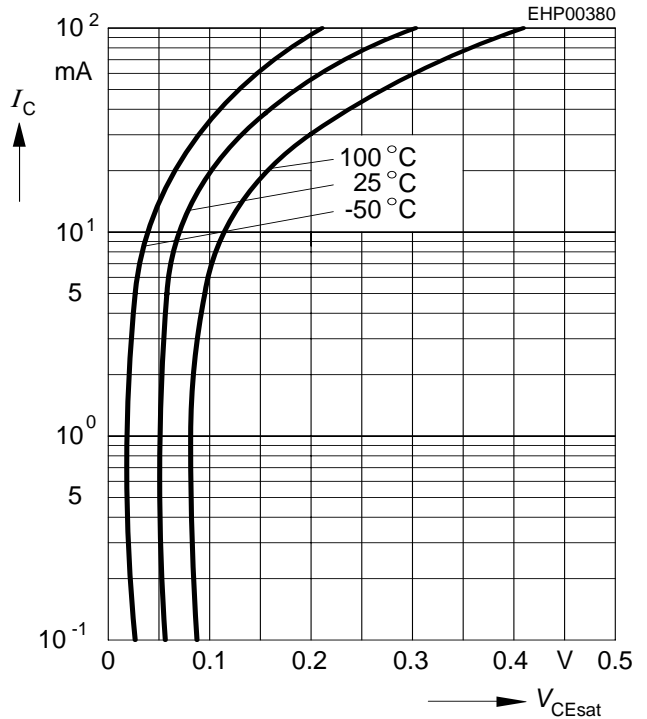
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$



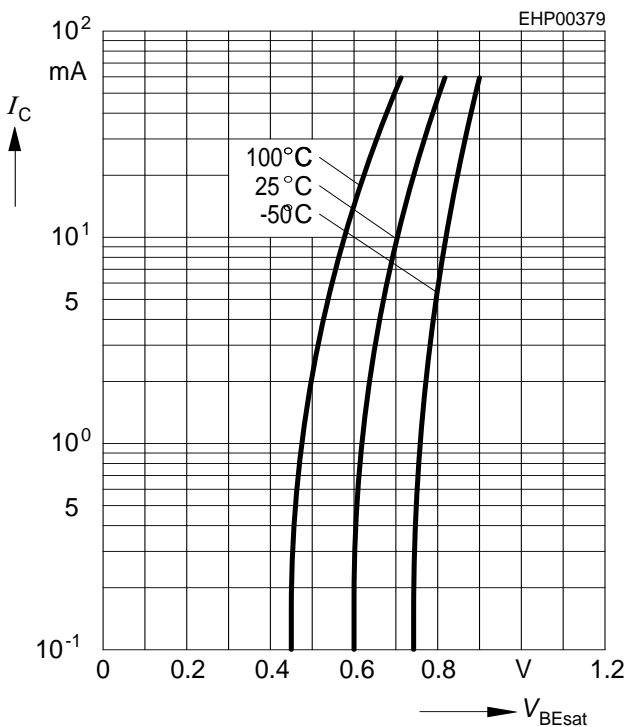
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 20$



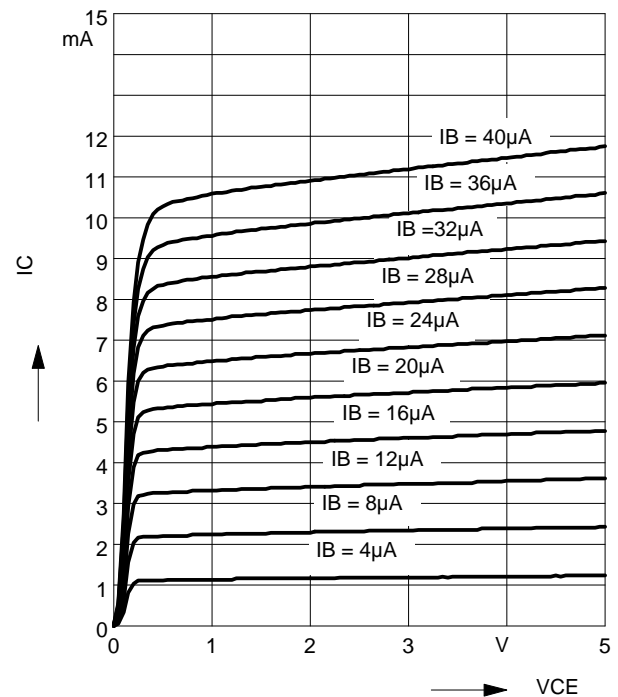
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 20$



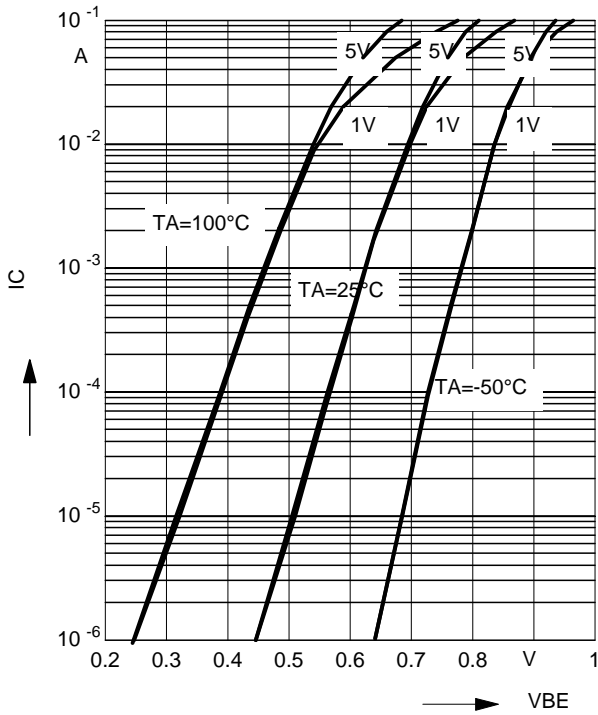
Output characteristics $I_C = f(V_{CE})$,

$I_B = \text{parameter}$



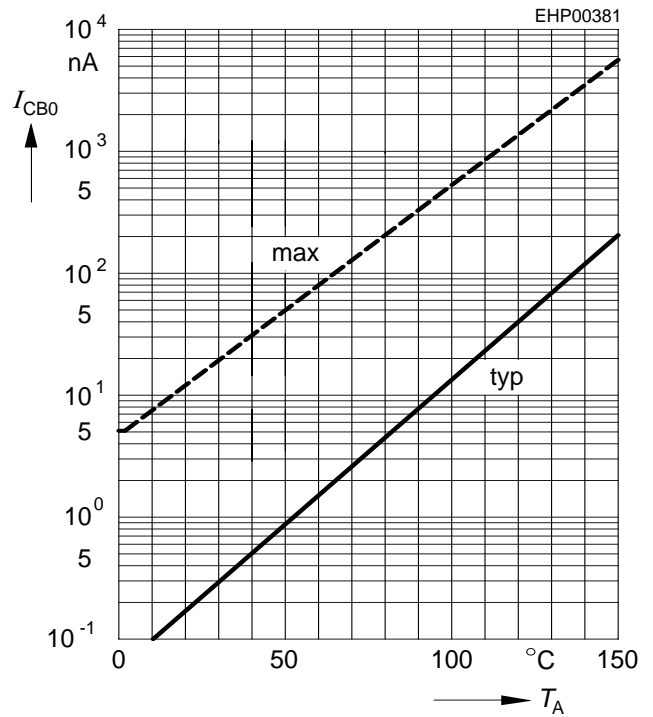
Collector current $I_C = f(V_{BE})$

$V_{CE} = \text{Parameter}$



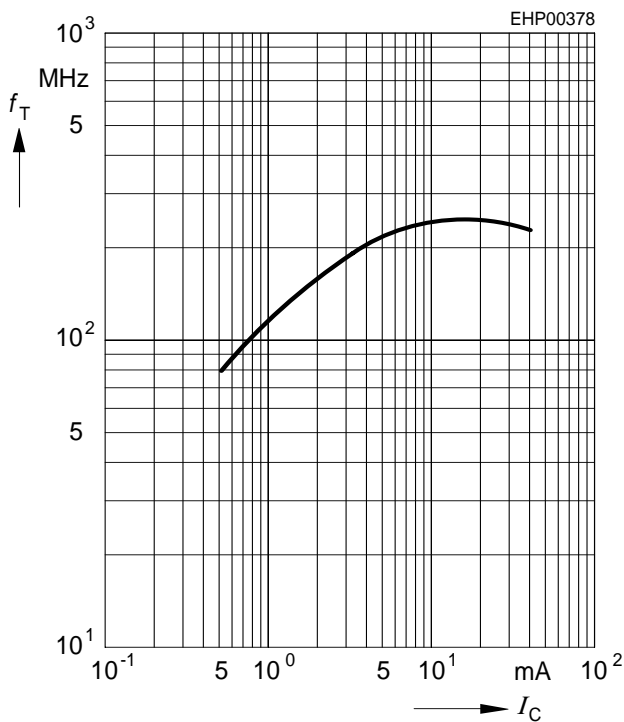
Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CBO} = 30 \text{ V}$



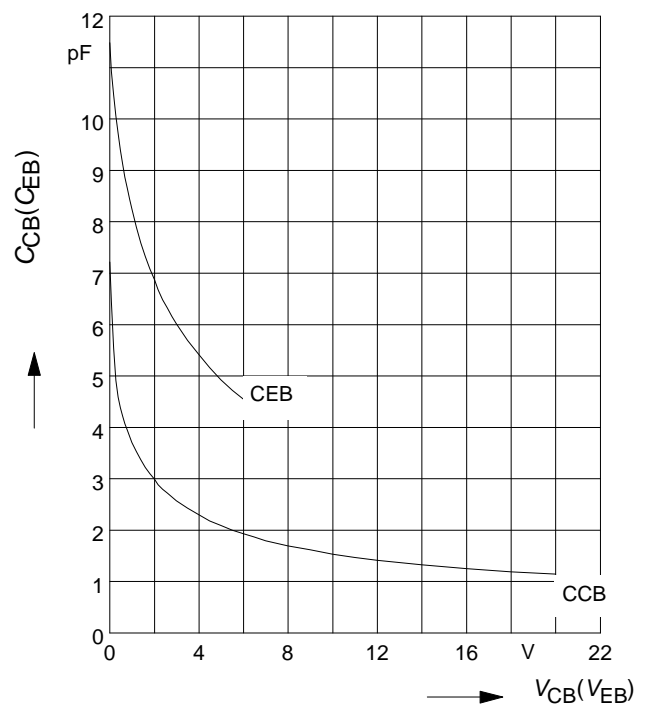
Transition frequency $f_T = f(I_C)$

$V_{CE} = \text{parameter in V, } f = 2 \text{ GHz}$

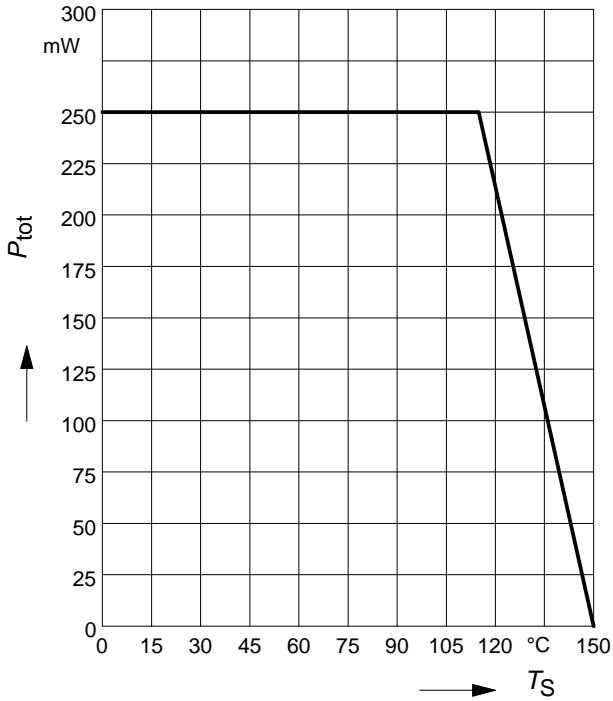


Collector-base capacitance $C_{cb} = f(V_{CB})$

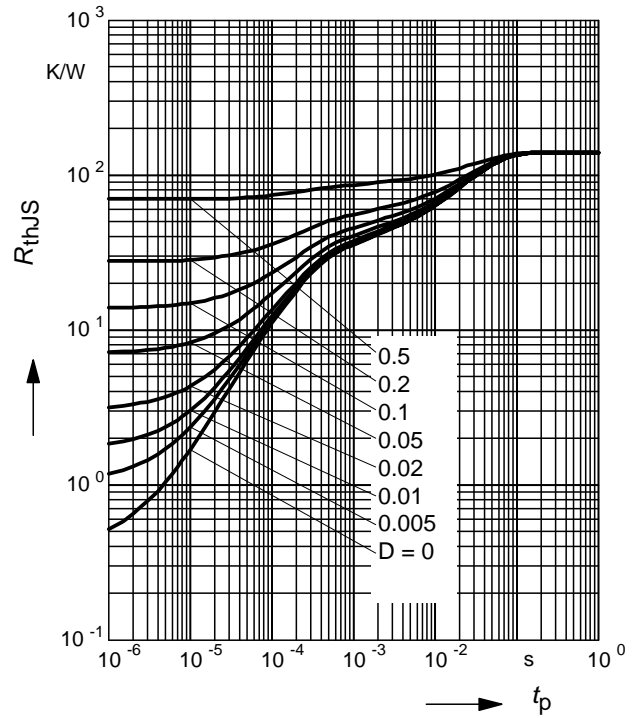
Emitter-base capacitance $C_{eb} = f(V_{EB})$



Total power dissipation $P_{tot} = f(T_S)$

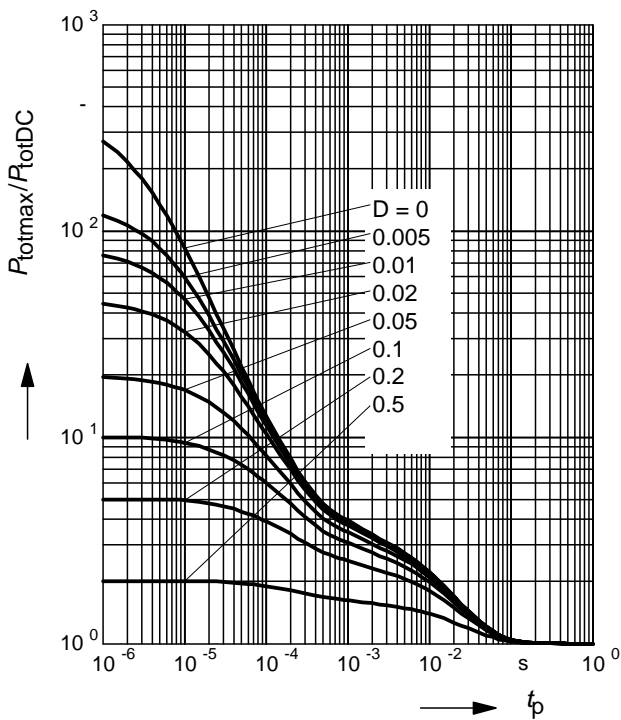


Permissible Pulse Load $R_{thJS} = f(t_p)$



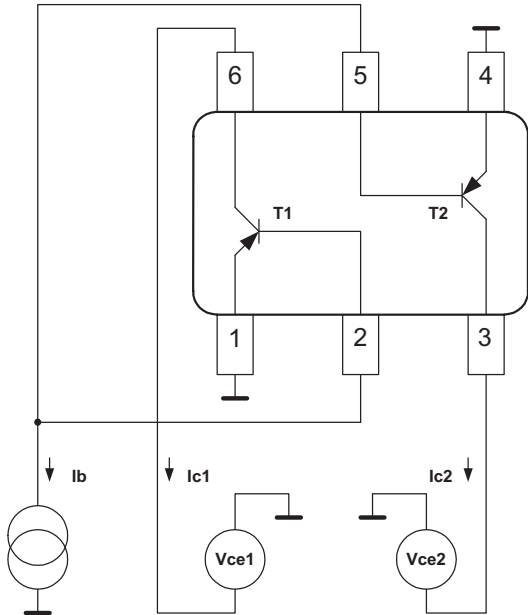
Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

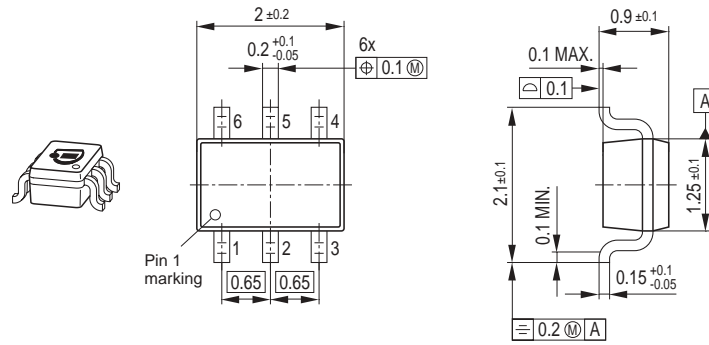


Definition of matching

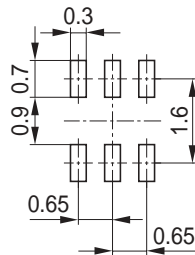
$$\Delta I_C = (I_{C2} - I_{C1}) / I_{C1}$$



Package Outline

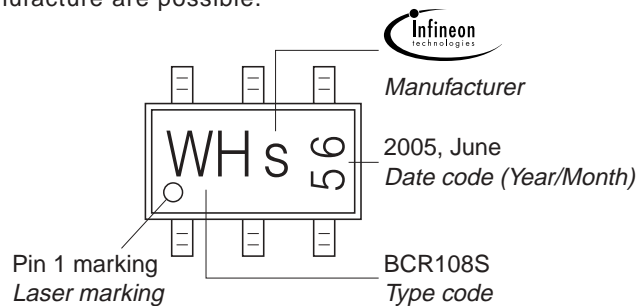


Foot Print



Marking Layout (Example)

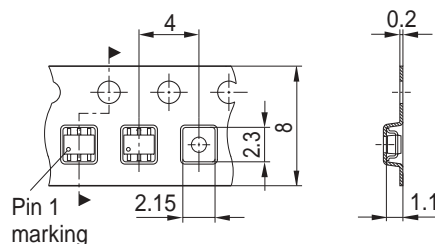
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



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